

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.016				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.022				
I _D (A)	- 8				
Configuration	Single				

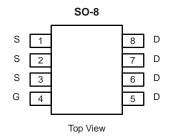
FEATURES

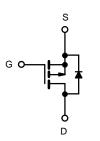
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Adaptor Switch
- Notebook





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 30	V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current	T _C = 25 °C	1	- 8		
	T _C = 125 °C	I _D	- 6.7		
Continuous Source Current (Diode Conduction)		I _S	- 6.2	Α	
Pulsed Drain Current ^a		I _{DM}	- 32		
Single Pulse Avalanche Current	1 0411	I _{AS}	- 25		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	31	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	6.8	14/	
	T _C = 125 °C		2.3	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	85	°C/W		
Junction-to-Foot (Drain)		R_{thJF}	22	C/VV		

- a. Surface mounted on 1" x 1" FR4 board.
- c. Maximum under steady state conditions is 80 °C/W. d. Based on $T_C = 25$ °C.



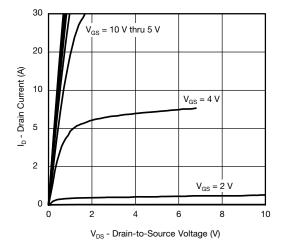
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		- 1	-	- 2.5	\ \
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1	μА
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 8	-	-	Α
		V _{GS} = - 10 V	I _D = - 8 A	-	0.013	0.016	Ω
Dunin Course On Chata Basistan and		V _{GS} = - 10 V	I _D = - 8 A, T _J = 125 °C	-	-	0.026	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 8 A, T _J = 175 °C	-	-	0.030	
		V _{GS} = - 4.5 V	I _D = - 6 A	-	0.016	0.022	
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 8 A		-	22	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = - 15 V, f = 1 MHz	-	1736	2170	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	392	490	
Reverse Transfer Capacitance	C _{rss}	7		-	268	335	
Total Gate Charge ^c	Qg			-	38.3	58	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -4.6 \text{ A}$	-	5.9	-	nC
Gate-Drain Charge ^c	Q _{gd}	7		-	9	-	
Gate Resistance	R _g	f = 1 MHz		2	-	7	Ω
Turn-On Delay Time ^c	t _{d(on)}				12.5	19	
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 15 Ω I_D \cong - 1 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	9	15	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	45.3	68	
Fall Time ^c	t _f			-	10	15	
Source-Drain Diode Ratings and Chara	acteristics ^b	•					
Pulsed Current ^a	I _{SM}			-	-	- 32	Α
Forward Voltage	V_{SD}	I _F = -8 A, V _{GS} = 0		-	- 0.84	- 1.2	V

Notes

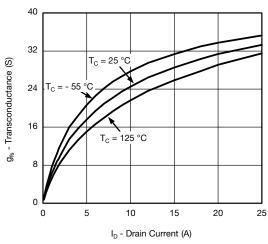
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

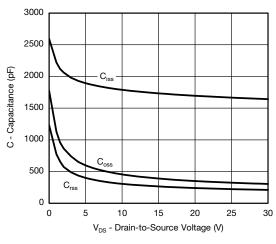
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



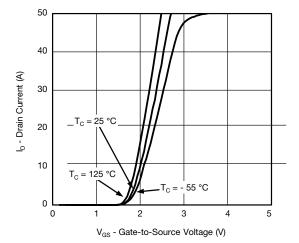
Output Characteristics



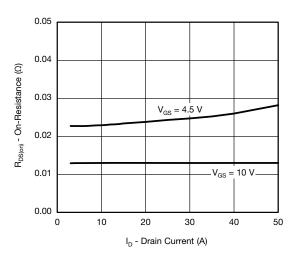
Transconductance



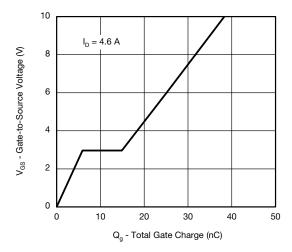
Capacitance



Transfer Characteristics



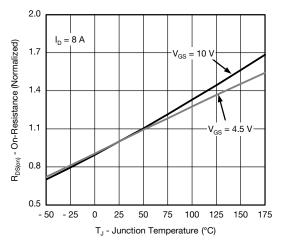
On-Resistance vs. Drain Current



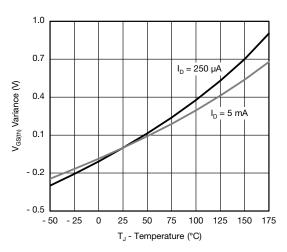
Gate Charge



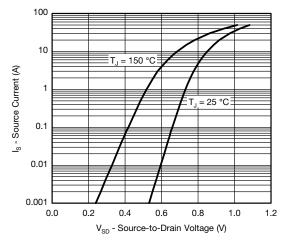
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



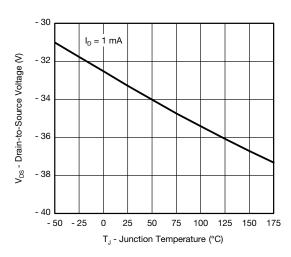
On-Resistance vs. Junction Temperature



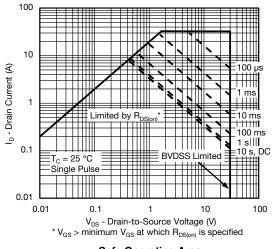
Threshold Voltage



Source Drain Diode Forward Voltage

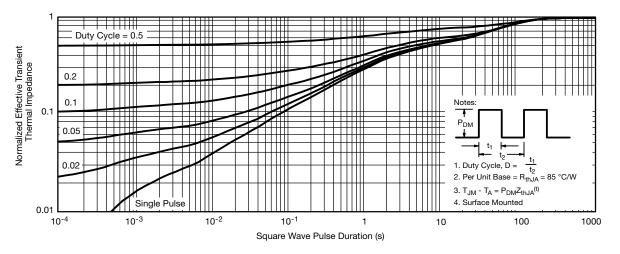


Drain Source Breakdown vs. Junction Temperature

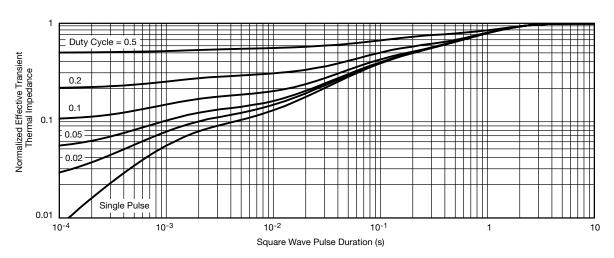


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



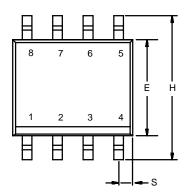
Normalized Thermal Transient Impedance, Junction-to-Foot

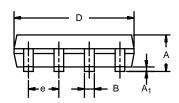
Note

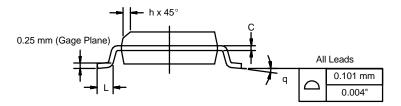
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





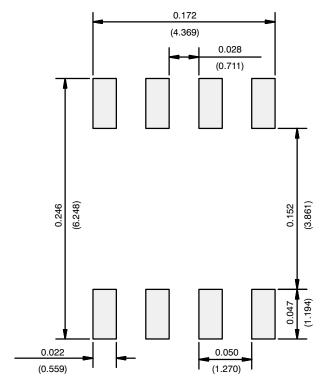


	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050) BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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